



NPN TIP110-111-112

SILICON DARLINGTON POWER TRANSISTORS

NPN epitaxial-base transistors in a monolithic Darlington circuit and housed in a TO-220 envelope.

They are designed for general purpose amplifier and low-speed switching applications.

PNP complements are TIP115-116-117

Compliance to RoHS-

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CBO}	Collector-Base Voltage	TIP110	60	V	
		TIP111	80		
		TIP112	100		
V_{CEO}	Collector-Emitter Voltage	TIP110	60	V	
		TIP111	80		
		TIP112	100		
V_{EBO}	Emitter-Base Voltage	TIP110	5	V	
		TIP111			
		TIP112			
I_C	Collector Current	TIP110	2	A	
		TIP111			
		TIP112			
I_{CM}	Collector Peak Current	TIP110	4	A	
		TIP111			
		TIP112			
I_B	Base Current	TIP110	50	mA	
		TIP111			
		TIP112			
P_T	Power Dissipation	@ $T_c < 25^\circ$	TIP110	50	Watts
			TIP111		
			TIP112		
		@ $T_a < 25^\circ$	TIP110	2	
			TIP111		
			TIP112		
T_J	Junction Temperature	TIP110	150	°C	
		TIP111			
		TIP112			
T_s	Storage Temperature range	TIP110	-65 to +150	°C	
		TIP111			
		TIP112			

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THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit	
$R_{thJ-case}$	From junction-case	TIP110	2.5	°C/W
		TIP111		
		TIP112		
$R_{thJ-amb}$	From junction-ambient	TIP110	62.5	°C/W
		TIP111		
		TIP112		

ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}C$ unless otherwise noted

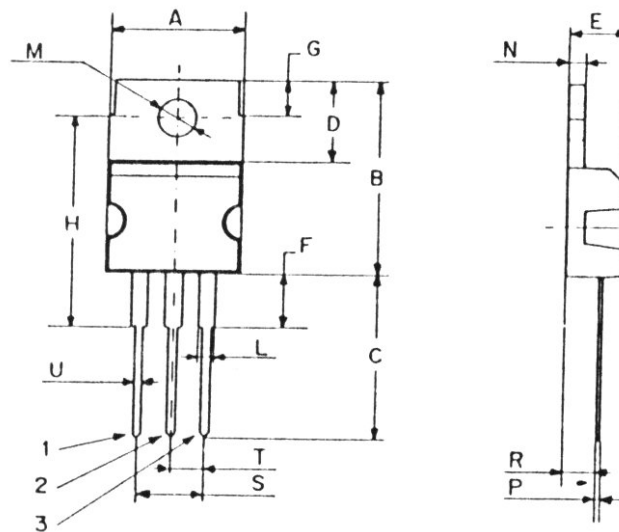
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
I_{CBO}	Collector Cutoff Current	$I_E=0, V_{CB}=V_{CB0max}$	TIP110	-	-	1	mA
			TIP111				
			TIP112				
I_{CEO}	Collector Cutoff Current	$I_E=0, V_{CE}=1/2 V_{CE0max}$	TIP110	-	-	2	mA
			TIP111				
			TIP112				
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5V, I_C=0$	TIP110	-	-	2	mA
			TIP111				
			TIP112				
V_{CEO}	Collector-Emitter Breakdown Voltage (*)	$I_C=30mA, I_B=0$	TIP110	60	-	-	V
			TIP111	80	-	-	
			TIP112	100	-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=2A, I_B=8mA$	TIP110	-	-	2.5	V
			TIP111				
			TIP112				
$V_{BE(on)}$	Base-Emitter Voltage (*)	$I_C=2A, V_{CE}=4V$	TIP110	-	-	2.8	V
			TIP111				
			TIP112				
h_{FE}	DC Current Gain (*)	$V_{CE}=4V, I_C=1A$	TIP110	1000	-	-	-
			TIP111				
			TIP112				
		$V_{CE}=4V, I_C=2A$	TIP110	500	-	-	
			TIP111				
			TIP112				
C_{OB}	Output Capacitance	$I_E=0, V_{CB}=10V$ $f=0.1MHz$	TIP110	-	-	100	pF
			TIP111				
			TIP112				

(*) Pulse Width $\approx 300 \mu s$, Duty Cycle $\angle 2.0\%$

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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Case :	Collector

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